BLF7G27L-200PB

Power LDMOS transistor

AMPLEON

Rev. 3 — 1 September 2015

Product data sheet

1. Product profile

1.1 General description

200 W LDMOS power transistor for base station applications at frequencies from 2600 MHz to 2700 MHz.

Table 1. Typical performance

Typical RF performance at T_{case} = 25 °C in a common source class-AB production test circuit.

| Mode of operation | f | I _{Dq} | V _{DS} | P _{L(AV)} | Gp | η _D | ACPR |
|-------------------|--------------|-----------------|-----------------|--------------------|------|----------------|----------------------|
| | (MHz) | (mA) | (V) | (W) | (dB) | (%) | (dBc) |
| 2-carrier W-CDMA | 2620 to 2690 | 1700 | 32 | 65 | 16.5 | 29 | -30 <mark>[1]</mark> |

^[1] Test signal: 3GPP; test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF; carrier spacing 5 MHz.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low R_{th} providing excellent thermal stability
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

RF power amplifiers for W-CDMA base stations and multi carrier applications in the 2600 MHz to 2700 MHz frequency range

2. Pinning information

Table 2. Pinning

| Pin | Description | | Simplified outline | Graphic symbol |
|------|-------------|------------|--------------------|----------------|
| 1 | drain1 | | | |
| 2 | drain2 | | 6 1 2 7 | 1 6, 7 |
| 3 | gate1 | | | 3 8,9 |
| 4 | gate2 | | 8 3 4 9 | |
| 5 | source | <u>[1]</u> | | 4 7 5 |
| 6, 7 | sense drain | | | 2 sym127 |
| 8, 9 | sense gate | | | 2 sym127 |

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

| Type number | Packag | Package | | |
|----------------|--------|---|----------|--|
| | Name | Description | Version | |
| BLF7G27L-200PB | - | flanged LDMOST ceramic package; 2 mounting holes; 8 leads | SOT1110A | |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|----------------------|------------|------|------|------|
| V_{DS} | drain-source voltage | | - | 65 | V |
| V _{GS} | gate-source voltage | | -0.5 | +13 | V |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Tj | junction temperature | | - | 200 | °C |

5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Тур | Unit |
|----------------------|--|---|------|------|
| R _{th(j-c)} | thermal resistance from junction to case | T_{case} = 80 °C; P_{L} = 65 W; V_{DS} = 32 V; I_{Dq} = 1700 mA | 0.22 | K/W |

6. Characteristics

Table 6. Characteristics

 $T_i = 25$ °C per section, unless otherwise specified.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|----------------------------------|--|------|------|------|------|
| V _{(BR)DSS} | drain-source breakdown voltage | $V_{GS} = 0 \text{ V}; I_D = 1.44 \text{ mA}$ | 65 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | V_{DS} = 10 V; I_{D} = 144 mA | 1.5 | 1.9 | 2.3 | V |
| I _{DSS} | drain leakage current | $V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$ | - | - | 2.8 | μА |
| I _{DSX} | drain cut-off current | $V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$ | - | 28 | - | Α |
| I _{GSS} | gate leakage current | V_{GS} = 11 V; V_{DS} = 0 V | - | - | 280 | nΑ |
| g _{fs} | forward transconductance | V_{DS} = 10 V; I_{D} = 7.2 A | - | 10.6 | - | S |
| $R_{DS(on)} \\$ | drain-source on-state resistance | $V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 5.04 \text{ A}$ | - | 0.1 | - | Ω |
| I_{Dq} | quiescent drain current | main transistor: | 1530 | 1700 | 1870 | mΑ |
| | | $V_{DS} = 32 V$ | | | | |
| | | sense transistor: | | | | |
| | | $I_{DS} = 31 \text{ mA}$ | | | | |
| | | $V_{DS} = 30.1 \text{ V}$ | | | | |

7. Test information

Remark: All testing performed in a class-AB production test circuit.

Table 7. Functional test information

Mode of operation: 2-carrier W-CDMA, PAR = 8.4 dB at 0.01 % probability on the CCDF, 3GPP test model 1; 1-64 DPCH; f_1 = 2622.5 MHz; f_2 = 2627.5 MHz; f_3 = 2682.5 MHz; f_4 = 2687.5 MHz; RF performance at V_{DS} = 32 V; I_{Dq} = 1700 mA; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-------------|------------------------------|------------|------|------|------|------|
| $P_{L(AV)}$ | average output power | | - | 65 | - | W |
| Gp | power gain | | 14.8 | 16.5 | 17.7 | dB |
| RLin | input return loss | | - | -15 | -5 | dB |
| η_{D} | drain efficiency | | 25.5 | 29 | - | % |
| ACPR | adjacent channel power ratio | | - | -30 | -27 | dBc |

7.1 Ruggedness in class-AB operation

The BLF7G27L-200PB is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 32 V; I_{Dq} = 1700 mA; P_{L} = 200 W (CW); f = 2600 MHz.

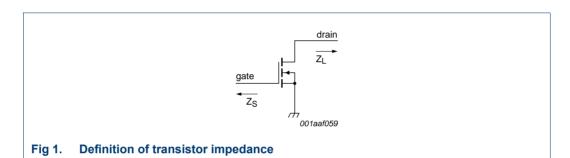
7.2 Impedance information

Table 8. Typical impedance

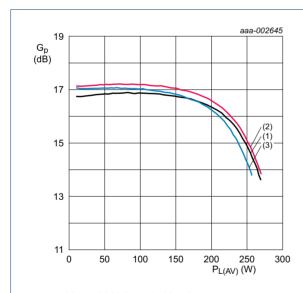
Measured load-pull data half device; $I_{Da} = 850 \text{ mA}$; $V_{DS} = 32 \text{ V}$.

| f | Z _S [1] | Z _L [1] |
|-------|--------------------|--------------------|
| (MHz) | (Ω) | (Ω) |
| 2500 | 3.07 – j3.51 | 2.79 – j4.86 |
| 2600 | 4.51 – j12.51 | 2.61 – j4.49 |
| 2700 | 7.56 – j15.0 | 2.36 – j4.41 |

[1] Z_S and Z_L defined in Figure 1.



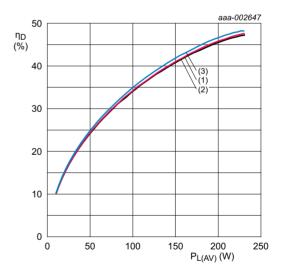
7.3 1 Tone CW





- (1) f = 2600 MHz
- (2) f = 2650 MHz
- (3) f = 2700 MHz

Fig 2. Power gain as a function of average load power; typical values

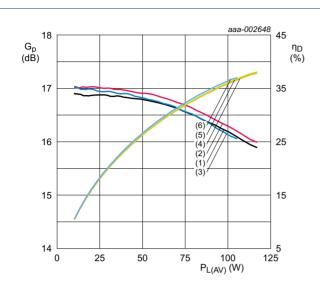


 V_{DS} = 32 V; I_{Dq} = 1700 mA.

- (1) f = 2600 MHz
- (2) f = 2650 MHz
- (3) f = 2700 MHz

Fig 3. Drain efficiency as a function of average load power; typical values

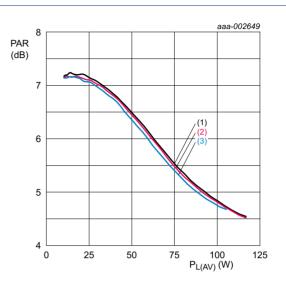
7.4 1-carrier W-CDMA



 V_{DS} = 32 V; I_{Dq} = 1700 mA; PAR = 7.2 dB at 0.01 % probability on the CCDF.

- (1) G_p ; f = 2620 MHz
- (2) G_p ; f = 2650 MHz
- (3) G_p ; f = 2690 MHz
- (4) η_D ; f = 2620 MHz
- (5) η_D ; f = 2650 MHz
- (6) η_D ; f = 2690 MHz

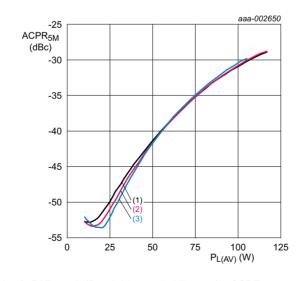
Fig 4. Power gain and drain efficiency as function of average load power; typical values



 V_{DS} = 32 V; I_{Dq} = 1700 mA; PAR = 7.2 dB at 0.01 % probability on the CCDF.

- (1) f = 2620 MHz
- (2) f = 2650 MHz
- (3) f = 2690 MHz

Fig 5. Peak-to-average power ratio as a function of peak power; typical values

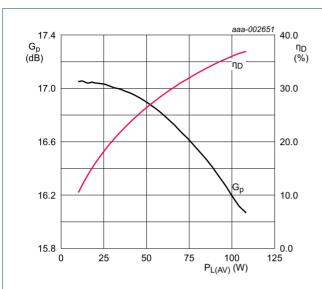


 V_{DS} = 32 V; I_{Dq} = 1700 mA; PAR = 7.2 dB at 0.01 % probability on the CCDF.

- (1) f = 2620 MHz
- (2) f = 2650 MHz
- (3) f = 2690 MHz

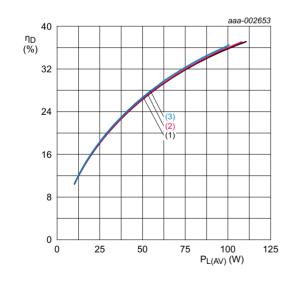
Fig 6. Adjacent power channel ratio (5 MHz) as a function of average load power; typical values

7.5 2-carrier W-CDMA



 $V_{DS}=32$ V; $I_{Dq}=1700$ mA; f = 2650 MHz; channel spacing = 5 MHz; PAR = 8.4 dB at 0.01 % probability on the CCDF.

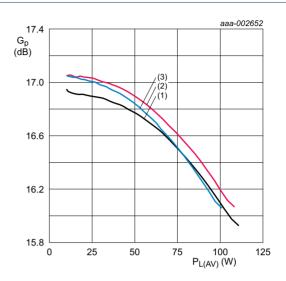
Fig 7. Power gain and drain efficiency as function of average load power; typical values



 V_{DS} = 32 V; I_{Dq} = 1700 mA; channel spacing = 5 MHz; PAR = 8.4 dB at 0.01 % probability on the CCDF.

- (1) f = 2620 MHz
- (2) f = 2650 MHz
- (3) f = 2690 MHz

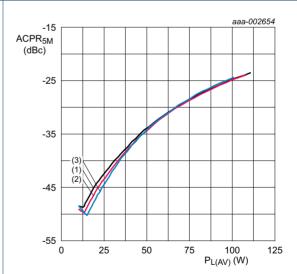
Fig 9. Drain efficiency as a function of average load power; typical values



 V_{DS} = 32 V; I_{Dq} = 1700 mA; channel spacing = 5 MHz; PAR = 8.4 dB at 0.01 % probability on the CCDF.

- (1) f = 2620 MHz
- (2) f = 2650 MHz
- (3) f = 2690 MHz

Fig 8. Power gain as a function of average load power; typical values

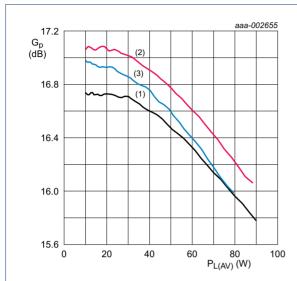


 V_{DS} = 32 V; I_{Dq} = 1700 mA; channel spacing = 5 MHz; PAR = 8.4 dB at 0.01 % probability on the CCDF.

- (1) f = 2620 MHz
- (2) f = 2650 MHz
- (3) f = 2690 MHz

Fig 10. Adjacent power channel ratio (5 MHz) as a function of average load power; typical values

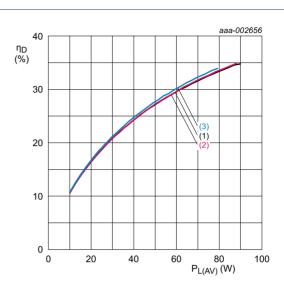
7.6 IS-95



$$V_{DS} = 32 \text{ V}; I_{Dq} = 1700 \text{ mA}.$$

- (1) f = 2600 MHz
- (2) f = 2650 MHz
- (3) f = 2700 MHz

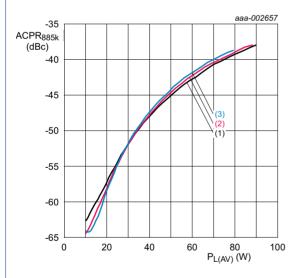
Fig 11. Single carrier IS-95 power gain as a function of average output power; typical values



$$V_{DS} = 32 \text{ V}; I_{Dq} = 1700 \text{ mA}.$$

- (1) f = 2600 MHz
- (2) f = 2650 MHz
- (3) f = 2700 MHz

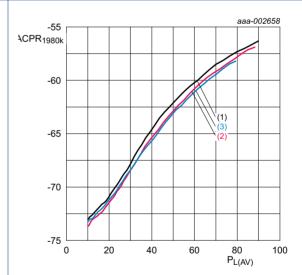
Fig 12. Single carrier IS-95 drain efficiency as a function of average load power; typical values



 $V_{DS} = 32 \text{ V}; I_{Dq} = 1700 \text{ mA}.$

- (1) f = 2600 MHz
- (2) f = 2650 MHz
- (3) f = 2700 MHz

Fig 13. Single carrier IS-95 ACPR at 885 kHz as a function of average output power; typical values



 $V_{DS} = 32 \text{ V}; I_{Dq} = 1700 \text{ mA}.$

- (1) f = 2600 MHz
- (2) f = 2650 MHz
- (3) f = 2700 MHz

Fig 14. Single carrier IS-95 at ACPR at 1980 kHz as a function of average output power; typical values

7.7 Test circuit

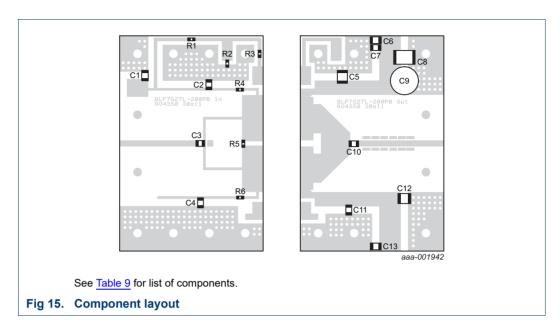


Table 9. List of components

See Figure 15 for component layout.

The used PCB material is Rogers RO4350B with a thickness of 0.76 mm.

| Component | Description | Value | Remarks |
|--------------|-----------------------------------|--------|--------------|
| C1, C6, C13 | multilayer ceramic chip capacitor | 4.7 μF | 11 Murata |
| C2, C4 | multilayer ceramic chip capacitor | 9.1 pF | 2 ATC100B |
| C3 | multilayer ceramic chip capacitor | 22 pF | 3 ATC100A |
| C5, C10, C11 | multilayer ceramic chip capacitor | 8.2 pF | 2 ATC100B |
| C7 | multilayer ceramic chip capacitor | 470 nF | [4] AVX |
| C8, C12 | multilayer ceramic chip capacitor | 10 μF | 5 TDK |
| C9 | electrolytic capacitor | 470 μF | |
| R1 | chip resistor | 820 Ω | Philips 0603 |
| R2 | chip resistor | 2Κ2 Ω | Philips 0603 |
| R3 | chip resistor | 22 Ω | Philips 0603 |
| R4, R6 | chip resistor | 10 Ω | Philips 0603 |
| R5 | chip resistor | 33 Ω | Philips 0603 |

- [1] Murata or capacitor of same quality.
- [2] American Technical Ceramics type 100B or capacitor of same quality.
- [3] American Technical Ceramics type 100A or capacitor of same quality.
- [4] AVX or capacitor of same quality.
- [5] TDK or capacitor of same quality.
- [6] Philips or resistor of same quality.

8. Package outline

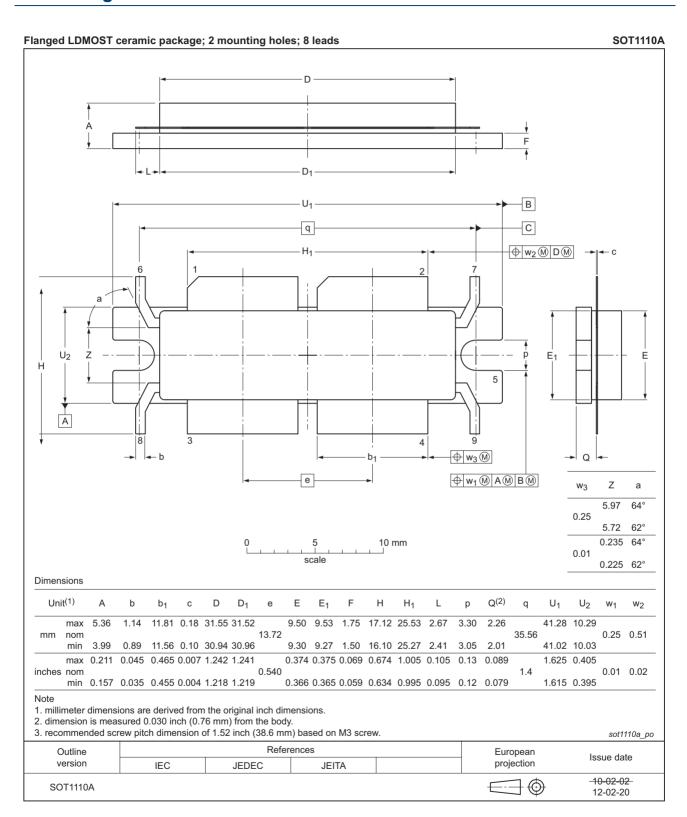


Fig 16. Package outline SOT1110A

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 10. Abbreviations

| Acronym | Description |
|---------|---|
| 3GPP | Third Generation Partnership Project |
| CCDF | Complementary Cumulative Distribution Function |
| CW | Continuous Wave |
| DPCH | Dedicated Physical CHannel |
| ESD | ElectroStatic Discharge |
| LDMOS | Laterally Diffused Metal Oxide Semiconductor |
| LDMOST | Laterally Diffused Metal Oxide Semiconductor Transistor |
| PAR | Peak-to-Average power Ratio |
| RF | Radio Frequency |
| VSWR | Voltage Standing Wave Ratio |
| W-CDMA | Wideband Code Division Multiple Access |

11. Revision history

Table 11. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes | |
|-------------------------------|--|----------------------|---------------|-----------------------------------|--|
| BLF7G27L-200PB#3 | 20150901 | Product data sheet | - | BLF7G27L-200PB v.2 | |
| Modifications: | The format of this document has been redesigned to comply with the new identity guidelines of Ampleon. Legal texts have been adapted to the new company name where appropriate. | | | | |
| BLF7G27L-200PB v.2 | 20120220 | Product data sheet | - | BLF7G27L-200PB_ 27LS-200PB v.1 | |
| BLF7G27L-200PB_27LS-200PB v.1 | 20110405 | Objective data sheet | - | - | |

12. Legal information

12.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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Power LDMOS transistor

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BLF7G27L-200PB

Power LDMOS transistor

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